TOSHIBA Transistor Silicon PNP Epitaxial Type (PCT process)

2SA1296

Power Amplifier Applications Power Switching Applications

- Low saturation voltage: $V_{CE (sat)} = -0.5 \text{ V (max)} @I_{C} = -2 \text{ A}$
- Complementary to 2SC3266.

Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	-20	V
Collector-emitter voltage	V _{CEO}	-20	V
Emitter-base voltage	V _{EBO}	-6	V
Collector current	Ic	-2	Α
Base current	Ι _Β	-0.5	А
Collector power dissipation	PC	750	mW
Junction temperature	Tj	150	°C
Storage temperature range	T _{stg}	-55~150	°C

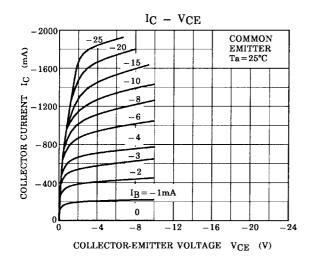
Weight: 0.21 g (typ.)

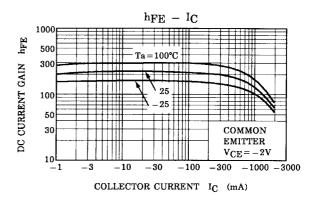
Electrical Characteristics (Ta = 25°C)

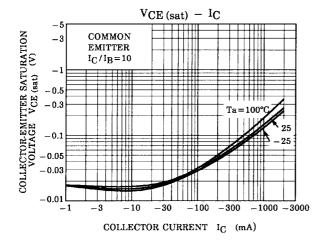
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Collector cut-off current	I _{CBO}	$V_{CB} = -20 \text{ V}, I_E = 0$	_	_	-0.1	μА
Emitter cut-off current	I _{EBO}	$V_{EB} = -6 \text{ V}, I_{C} = 0$	_	_	-0.1	μΑ
Collector-emitter breakdown voltage	V (BR) CEO	$I_C = -10 \text{ mA}, I_B = 0$	-20	_	_	V
Emitter-base breakdown voltage	V (BR) EBO	$I_E = -0.1 \text{ mA}, I_C = 0$	-6		_	٧
DC current gain	h _{FE (1)} (Note)	$V_{CE} = -2 \text{ V}, I_{C} = -0.1 \text{ A}$	120		400	
	h _{FE} (2)	$V_{CE} = -2 \text{ V}, I_{C} = -2 \text{ A}$	40	_	_	
Collector-emitter saturation voltage	V _{CE} (sat)	$I_C = -2 \text{ A}, I_B = -0.1 \text{ A}$	_	_	-0.5	V
Base-emitter voltage	V _{BE}	$V_{CE} = -2 \text{ V}, I_{C} = -0.1 \text{ A}$	_	_	-0.85	V
Transition frequency	f _T	$V_{CE} = -2 \text{ V}, I_{C} = -0.5 \text{ A}$	_	120	_	MHz
Collector output capacitance	C _{ob}	$V_{CB} = -10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$	_	40	_	pF

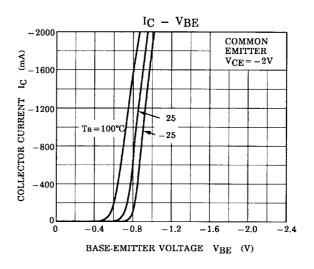
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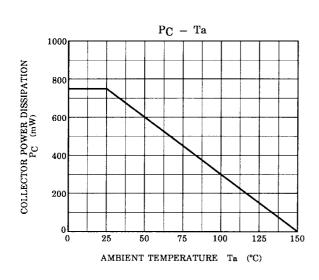
Note: hFE (1) Y: 120~240, GR: 200~400

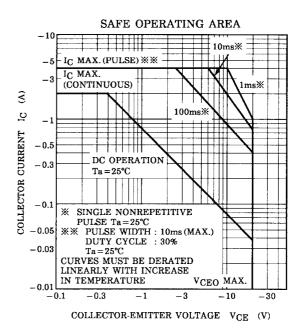












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